



Silicon Carbide Schottky Diode

Features

- χ Positive temperature coefficient
- χ Temperature-independent switching
- χ Maximum working temperature at 175 ÅC



ΩElectrical Characteristics (Per Leg)

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Typ.	Max.
------------	--------	------	-----------------	------	------

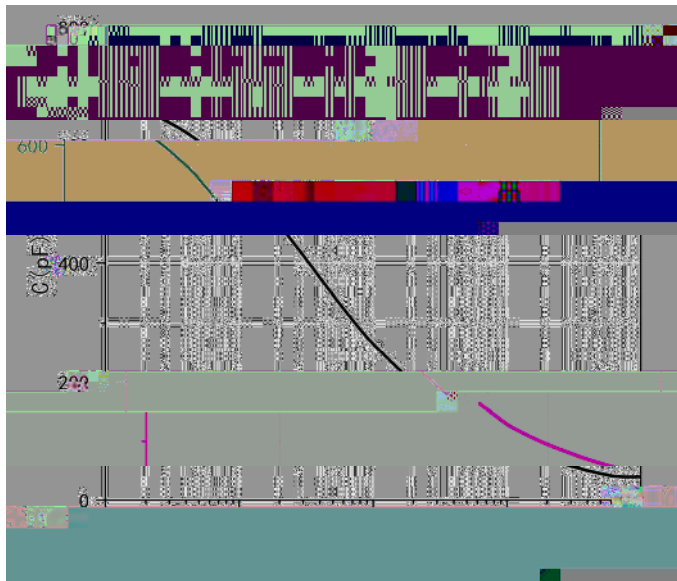


Figure 3. Capacitance vs. Reverse Voltage

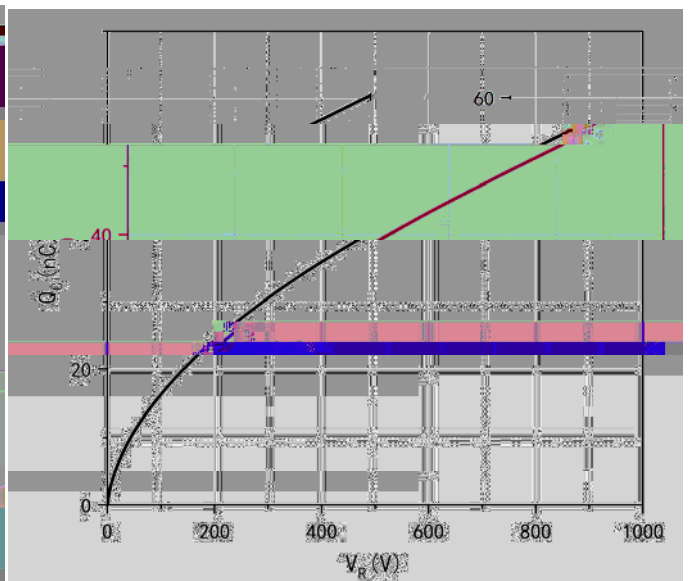


Figure 4. Total Capacitance Charge vs. Reverse Voltage

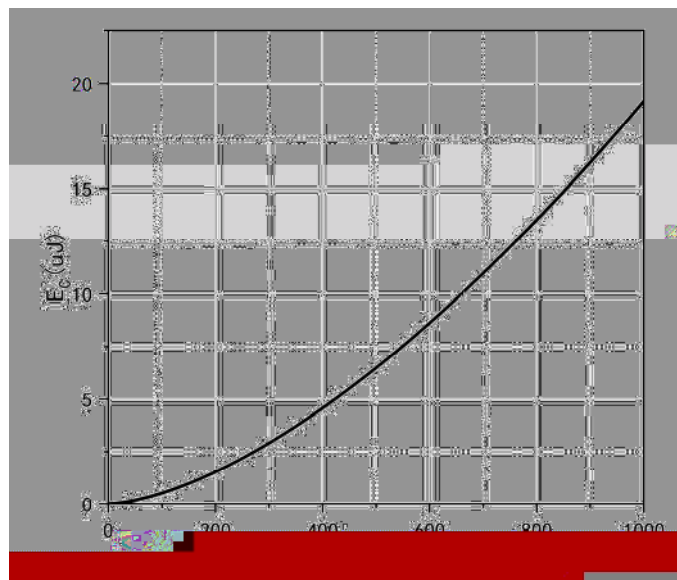


Figure 5. Capacitance Stored Energy

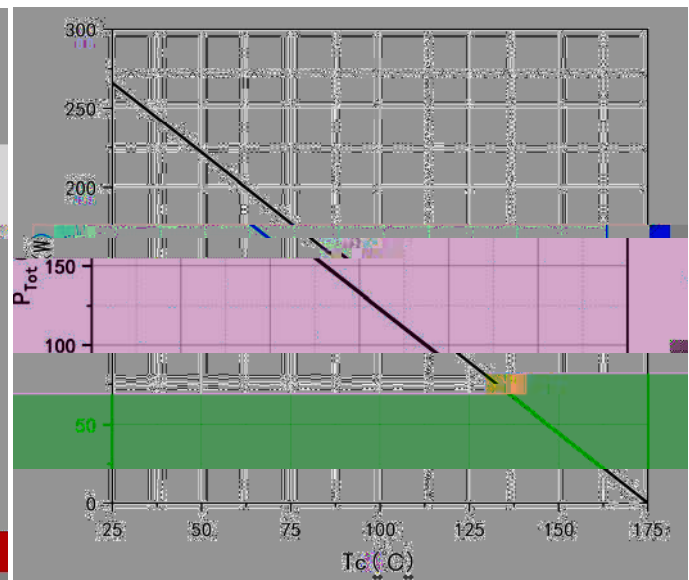


Figure 6. Power Derating

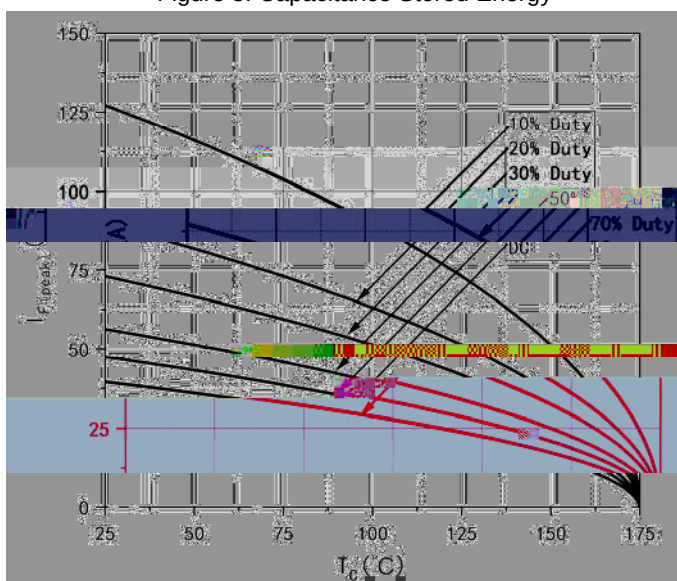


Figure 7. Current Derating



Ω Typical Characteristics (Device)

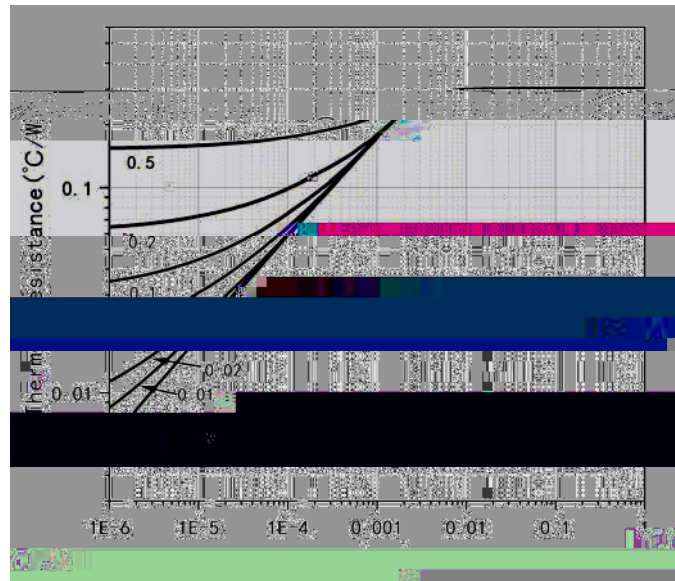


Figure 8. Transient Thermal Impedance



ΩOutline Dimensions

TO-247AB		
Dim	Min	Max
A	4.80	5.20

A1



Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic